

PROGRAMMING OF A FLASH MEMORY CELLABSTRACT OF THE DISCLOSURE

5 A method of programming a memory device comprises applying a first programming voltage to one of a plurality of wordlines, corresponding to a cell to be programmed. The first programming voltage is substantially equal to the desired threshold voltage. A second programming voltage is also applied to one of a plurality of bitlines, corresponding to the cell to be programmed. The second programming voltage gradually increases from a low level toward a high level. The first programming voltage and second programming voltage are removed when the corresponding bitline current begins to decrease.

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